Docket No.

242189US2S

# IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

Tsuneo INABA

SERIAL NO: NEW APPLICATION

GAU:

**EXAMINER:** 

FILED: FOR:

HEREWITH

MAGNETIC MEMORY DEVICE

# INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313

Applicant(s) wish to disclose the following information.

## REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

# **RELATED CASES**

- Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- A check is attached in the amount required under 37 CFR §1.17(p).

## CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

## **DEPOSIT ACCOUNT**

Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment form is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND, MAIER & N

Marvin J. Spivak

Registration No. 24,913

22850

Tel. (703) 413-3000 Fax. (703) 413-2220 (OSMMN 05/03)

Form PTO 1449 (Modified)			ATTY DOCKET NO. 242189US2S		SERIAL NO. NEW APPLICATION			
			APPLICANT					
LIST OF REFERENCES CITED BY APPLICANT								
				FILING DATE		GROUCOPY		
				HEREWITH				
				U.S. PATENT DOCUMENTS		<u> </u>		
		BOOLUENT		1	1	CUD	511 NO 5475	
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	AA				ļ			
	AB							
	AC							
	ΑĎ							
	ΑE							
	AF							
	AG							
	AH		•					
	Al							
	AJ					-		
	AK				İ			
	AL				<b>i</b> .			
	AM						-	
	AN							
			FO	REIGN PATENT DOCUMENTS	1			
		DOCUMENT NUMBER	DATE	COUNTRY	COUNTRY		TRANSLATION YES NO	
-	AO							
	AP							
	AQ							
	AR					1		
	AS					i	V	
	AT							
	AU		····					
	AV							
		OTHER REEL	ERENCES (	Including Author, Title, Date, Pertinen	t Pages, e	tc.)		
-							Tunnel Junction and FET	
	AW	Roy SCHEUERLEIN, et al., " A10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell" IEEE International Solid State Circuits Conference(ISSCC) Digest of Technical Papers, pp. 128-129, February 8, 2000						
	AX	M. Durlam, et al., "Nonvolatile RAM based on Magnetic Tunnel Junction Elements", IEEE International Solid-State Circuits Conference, (ISSCC) Digest of Technical Papers, pp. 130-131, February 8, 2000						
	AY	Peter K. Naji, et al., "A 256kb 3.0V 1T1MTJ Nonvolatile Magnetoresistive RAM", IEEE International Solid-State Circuits Conference (ISSCC) Digest of Technical Papers, pp. 122-123, February 6, 2001						
	AZ				Additional References sheet(s) attached			
Examiner					Date Considered			
*Examiner: In	itial if r	eference is considered, what considered, Include con	hether or no	t citation is in conformance with MPEP 6	09; Draw li	ine through	citation if not in	